

FEATURES

- 10µs Short Circuit Withstand
- High Thermal Cycling Capability
- Soft Punch Through Silicon
- Isolated AISiC Base with AlN Substrates
- Lead Free Construction

APPLICATIONS

- Motor Controllers
- Power Supplies
- Choppers

The Powerline range of high power modules includes half bridge, chopper, dual, single and bi-directional switch configurations covering voltages from 1200V to 6500V and currents up to 2400A.

The DIM800ECM33-F000 is a 3300V, soft punch through n-channel enhancement mode, insulated gate bipolar transistor (IGBT) chopper module. The IGBT has a wide reverse bias safe operating area (RBSOA) plus 10µs short circuit withstand. This device is optimised for traction drives and other applications requiring high thermal cycling capability.

The module incorporates an electrically isolated base plate and low inductance construction enabling circuit designers to optimise circuit layouts and utilise grounded heat sinks for safety.

ORDERING INFORMATION

Order As:

DIM800ECM33-F000

Note: When ordering, please use the complete part number

KEY PARAMETERS

V_{CES}	3300V
$V_{CE(sat)}$ * (typ)	2.8V
I_C (max)	800A
$I_{C(PK)}$ (max)	1600A

* Measured at the auxiliary terminals

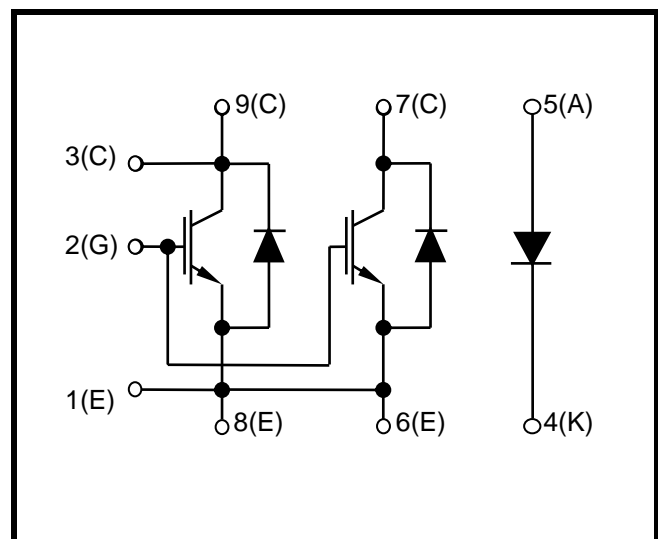


Fig. 1 Circuit configuration



Outline type code: E

(See Fig. 11 for further information)

Fig. 2 Package

ABSOLUTE MAXIMUM RATINGS

Stresses above those listed under ‘Absolute Maximum Ratings’ may cause permanent damage to the device. In extreme conditions, as with all semiconductors, this may include potentially hazardous rupture of the package. Appropriate safety precautions should always be followed. Exposure to Absolute Maximum Ratings may affect device reliability.

T_{case} = 25°C unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
V _{CES}	Collector-emitter voltage	V _{GE} = 0V	3300	V
V _{GES}	Gate-emitter voltage		±20	V
I _C	Continuous collector current	T _{case} = 90°C	800	A
I _{C(PK)}	Peak collector current	1ms, T _{case} = 115°C	1600	A
P _{max}	Max. transistor power dissipation	T _{case} = 25°C, T _j = 150°C	10400	W
I ² t	Diode I ² t value (IGBT arm)	V _R = 0, t _p = 10ms, T _j = 125°C	320	kA ² s
	Diode I ² t value (Diode arm)		320	kA ² s
V _{isol}	Isolation voltage – per module	Commoned terminals to base plate. AC RMS, 1 min, 50Hz	6000	V
Q _{PD}	Partial discharge – per module	IEC1287, V ₁ = 3500V, V ₂ = 2600V, 50Hz RMS	10	pC

THERMAL AND MECHANICAL RATINGS

Internal insulation material: AIN
 Baseplate material: AISiC
 Creepage distance: 31mm
 Clearance: 20mm
 CTI (Comparative Tracking Index): >600

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Units
R _{th(j-c)}	Thermal resistance – transistor (per arm)	Continuous dissipation – junction to case	-	-	12	°C/kW
R _{th(j-c)}	Thermal resistance – diode (IGBT arm)	Continuous dissipation – junction to case	-	-	24	°C/kW
	Thermal resistance – diode (Diode arm)		-	-	24	°C/kW
R _{th(c-h)}	Thermal resistance – case to heatsink (per module)	Mounting torque 5Nm (with mounting grease)	-	-	6	°C/kW
T _j	Junction temperature	Transistor	-	-	150	°C
		Diode	-	-	125	°C
T _{stg}	Storage temperature range	-	-40	-	125	°C
	Screw torque	Mounting – M6	-	-	5	Nm
		Electrical connections – M4	-	-	2	Nm
		Electrical connections – M8	-	-	10	Nm

ELECTRICAL CHARACTERISTICS
T_{case} = 25°C unless stated otherwise.

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
I _{CES}	Collector cut-off current	V _{GE} = 0V, V _{CE} = V _{CES}			4	mA
		V _{GE} = 0V, V _{CE} = V _{CES} , T _{case} = 125°C			60	mA
I _{GES}	Gate leakage current	V _{GE} = ± 20V, V _{CE} = 0V			1	µA
V _{GE(TH)}	Gate threshold voltage	I _C = 80mA, V _{GE} = V _{CE}	5.5	6.5	7.0	V
V _{CE(sat)} †	Collector-emitter saturation voltage	V _{GE} = 15V, I _C = 800A		2.8		V
		V _{GE} = 15V, I _C = 800A, T _j = 125°C		3.6		V
I _F	Diode forward current	DC		800		A
I _{FM}	Diode maximum forward current	t _p = 1ms		1600		A
V _F †	Diode forward voltage (IGBT arm)	I _F = 800A		2.9		V
	Diode forward voltage (Diode arm)			2.9		V
	Diode forward voltage (IGBT arm)	I _F = 800A, T _j = 125°C		3.0		V
	Diode forward voltage (Diode arm)			3.0		V
C _{ies}	Input capacitance	V _{CE} = 25V, V _{GE} = 0V, f = 1MHz		144		nF
Q _g	Gate charge	±15V		20		µC
C _{res}	Reverse transfer capacitance	V _{CE} = 25V, V _{GE} = 0V, f = 1MHz		2.2		nF
L _M	Module inductance – IGBT arm			15		nH
R _{INT}	Internal resistance – IGBT arm			135		µΩ
SC _{Data}	Short circuit current, I _{SC}	T _j = 125°C, V _{CC} = 2500V t _p ≤ 10µs, V _{GE} ≤ 15V V _{CE(max)} = V _{CES} – L* x di/dt IEC 60747-9		3700		A

Note:

† Measured at the auxiliary terminals

* L is the circuit inductance + L_M

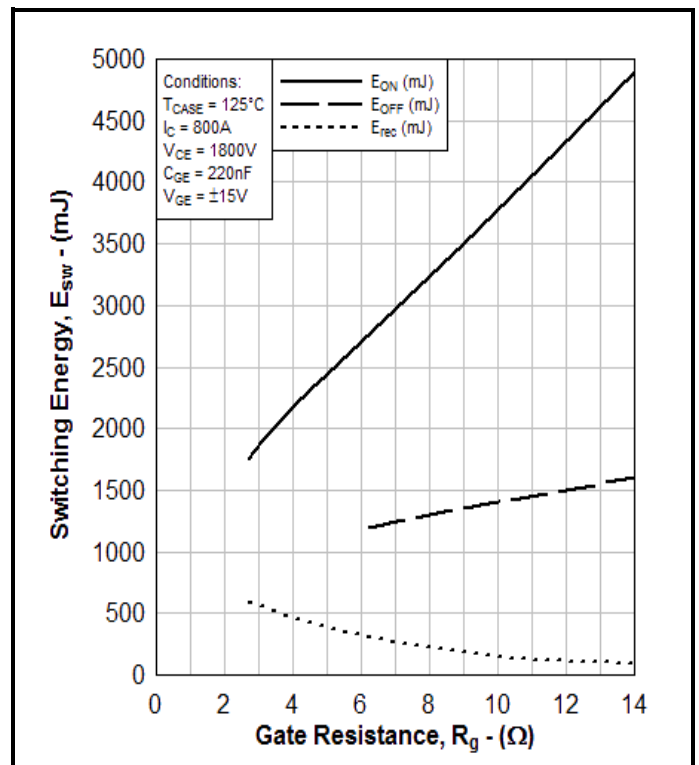
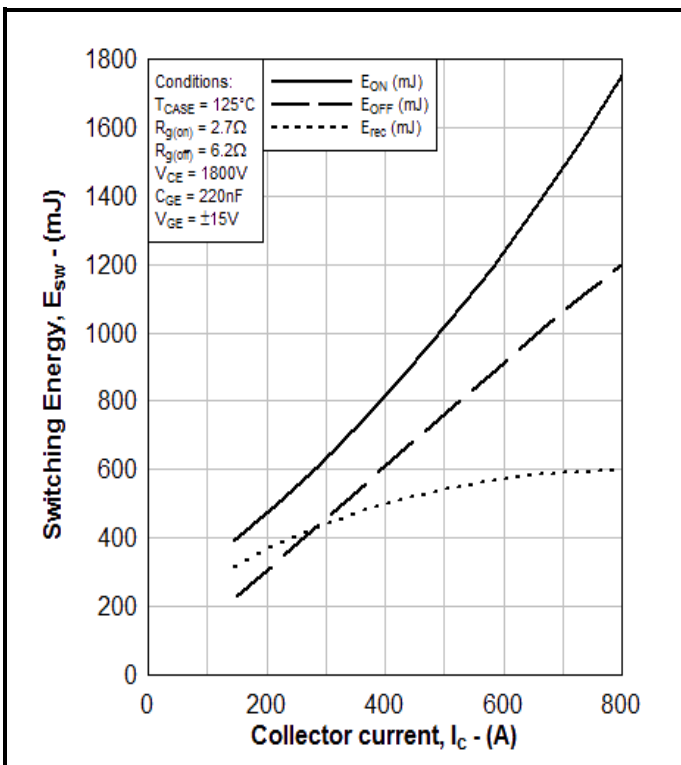
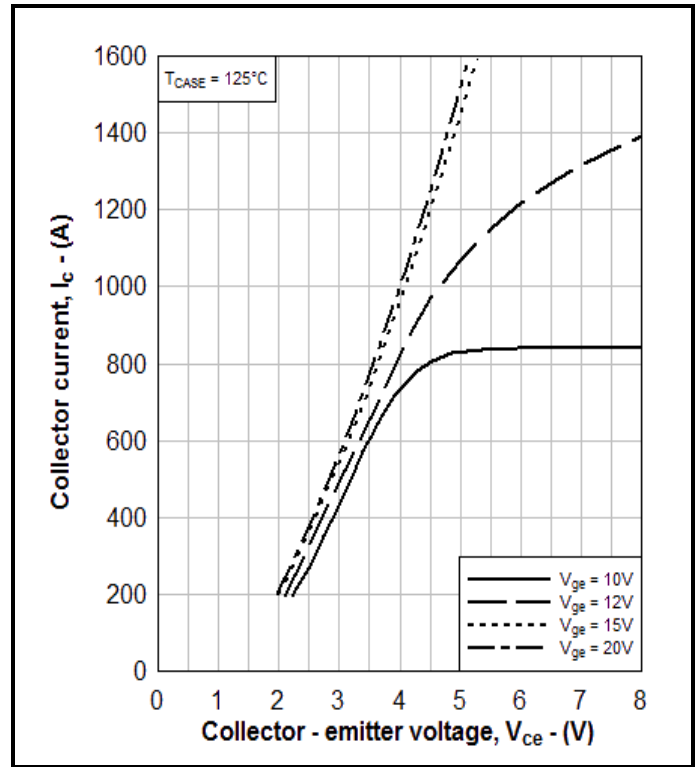
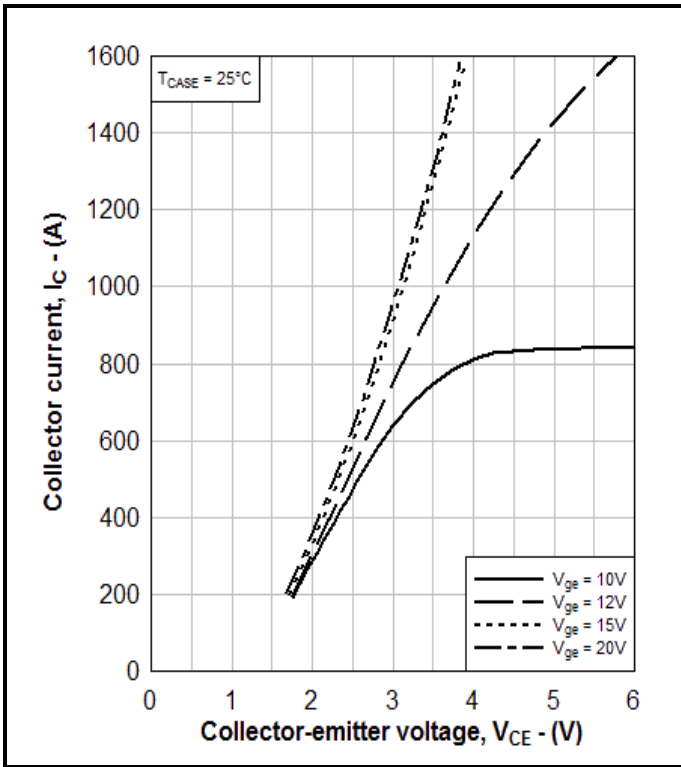
ELECTRICAL CHARACTERISTICS

$T_{\text{case}} = 25^{\circ}\text{C}$ unless stated otherwise

Symbol	Parameter	Test Conditions		Min	Typ.	Max	Units
$t_{d(\text{off})}$	Turn-off delay time	$I_C = 800\text{A}$ $V_{GE} = \pm 15\text{V}$ $V_{CE} = 1800\text{V}$ $C_{ge} = 220\text{nF}$ $L_S \sim 100\text{nH}$	$R_{G(\text{ON})} = 3.9\Omega$ $R_{G(\text{OFF})} = 6.2\Omega$		3.0		μs
t_f	Fall time				270		ns
E_{OFF}	Turn-off energy loss				1050		mJ
$t_{d(\text{on})}$	Turn-on delay time				1300		ns
t_r	Rise time				275		ns
E_{ON}	Turn-on energy loss		$R_{G(\text{ON})} = 2.7\Omega$ $R_{G(\text{OFF})} = 6.2\Omega$		1250		mJ
Q_{rr}	Diode reverse recovery charge	$I_F = 800\text{A}$ $V_{CE} = 1800\text{V}$ $di_F/dt = 4000\text{A}/\mu\text{s}$			320		μC
I_{rr}	Diode reverse recovery current				670		A
E_{rec}	Diode reverse recovery energy				300		mJ

$T_{\text{case}} = 125^{\circ}\text{C}$ unless stated otherwise

Symbol	Parameter	Test Conditions		Min	Typ.	Max	Units
$t_{d(\text{off})}$	Turn-off delay time	$I_C = 800\text{A}$ $V_{GE} = \pm 15\text{V}$ $V_{CE} = 1800\text{V}$ $C_{ge} = 220\text{nF}$ $L_S \sim 100\text{nH}$	$R_{G(\text{ON})} = 3.9\Omega$ $R_{G(\text{OFF})} = 6.2\Omega$		3.1		μs
t_f	Fall time				280		ns
E_{OFF}	Turn-off energy loss				1200		mJ
$t_{d(\text{on})}$	Turn-on delay time				1200		ns
t_r	Rise time				315		ns
E_{ON}	Turn-on energy loss		$R_{G(\text{ON})} = 2.7\Omega$ $R_{G(\text{OFF})} = 6.2\Omega$			1750	
Q_{rr}	Diode reverse recovery charge	$I_F = 800\text{A}$ $V_{CE} = 1800\text{V}$ $di_F/dt = 4000\text{A}/\mu\text{s}$			600		μC
I_{rr}	Diode reverse recovery current				800		A
E_{rec}	Diode reverse recovery energy				600		mJ



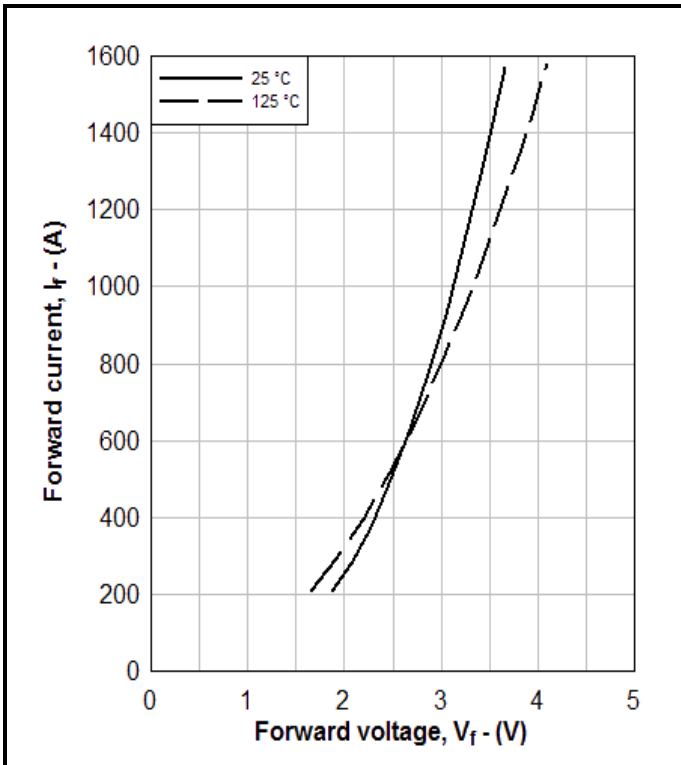


Fig. 7 Diode typical forward characteristics

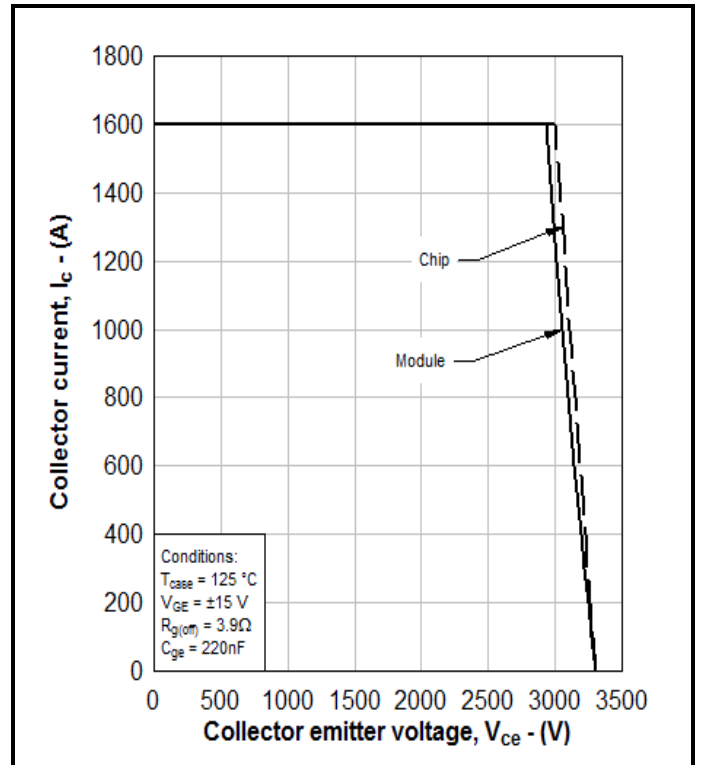


Fig. 8 Reverse bias safe operating area

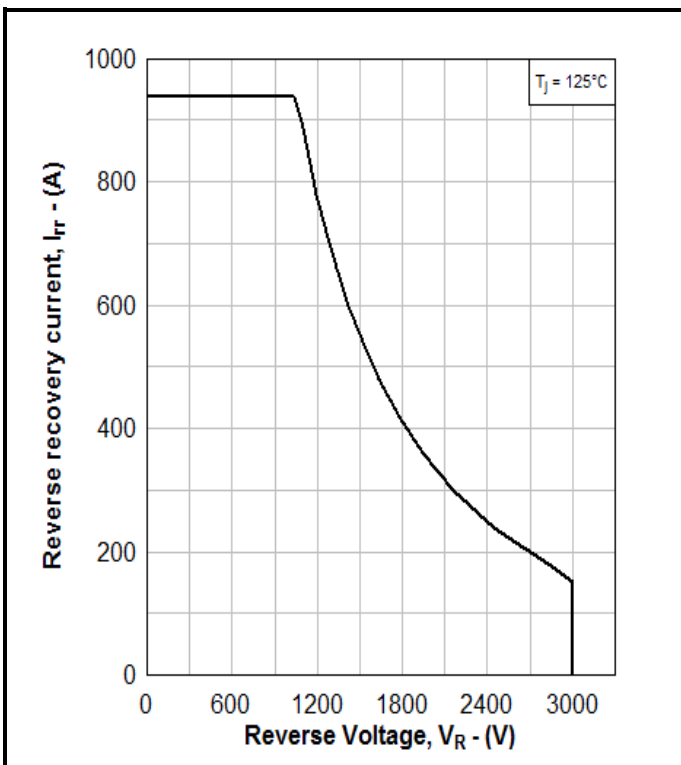


Fig. 9 Diode reverse bias safe operating area

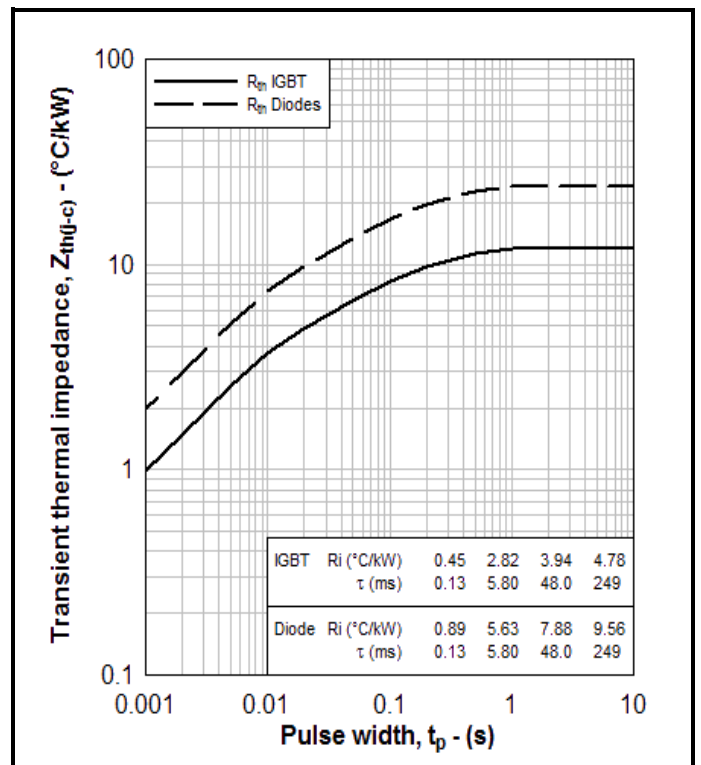
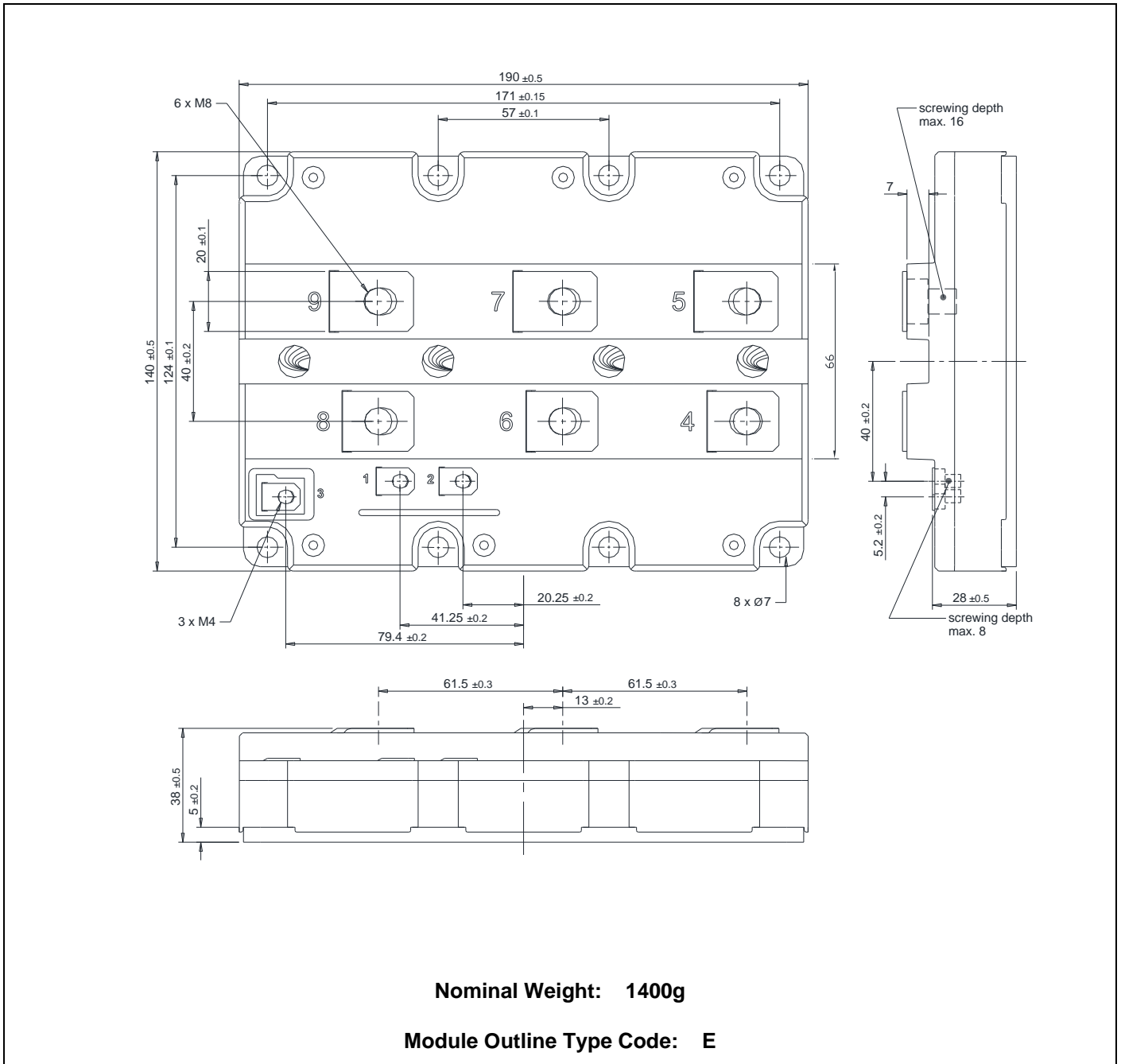


Fig. 10 Transient thermal impedance

PACKAGE DETAILS

For further package information, please visit our website or contact Customer Services.
 All dimensions in mm, unless stated otherwise.
DO NOT SCALE.


Fig. 11 Module outline drawing

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